1 GHz, 25 dB gain GaAs high output power doublerRev. 1 — 5 April 2011Product

Product data sheet

Product profile 1.

1.1 General description

Hybrid amplifier module in a SOT115J package, operating at a supply voltage of 24 V Direct Current (DC), employing Hetero junction Field Effect Transistor (HFET) GaAs dies.

1.2 Features and benefits

- Excellent linearity
- Optimized for flat PAL D and flat NTSC loading
- Superior levels of ESD protection
- Extremely low noise
- Excellent return loss properties
- Gain compensation over temperature
- Rugged construction
- Unconditionally stable
- Thermally optimized design
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)
- Integrated ring wave surge protection

1.3 Applications

CATV systems operating in the 40 MHz to 862 MHz / 1003 MHz frequency range using PAL D or NTSC channel conditions.

1.4 Quick reference data

Quick reference data Table 1.

Bandwidth 40 MHz to 1003 MHz; $V_B = 24 V (DC)$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35$ °C; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Gp	power gain	f = 50 MHz		-	23.2	-	dB
		f = 1003 MHz		23.5	24.4	25.5	dB
CTB	composite triple beat	$V_o = 48 \text{ dBmV}$ at 862 MHz	[1]	-	-66	-62	dBc
CSO	composite second-order distortion	$V_o = 48 \text{ dBmV}$ at 862 MHz	[1]	-	-69	-62	dBc
I _{tot}	total current		[2]	-	440	460	mA

[1] 98 PAL D channels with 8 MHz bandwidth per channel; [f = 47 MHz to 862 MHz]; flat V_0 till 862 MHz.

[2] Direct Current (DC).



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2. Pinning information

Table 2.	Pinning	
Pin	Description	Simplified outline Graphic symbol
1	input	
2, 3	common	
5	+V _B	
7, 8	common	
9	output	sym095

3. Ordering information

Table 3. Ordering information				
Type number	Packag	je		
	Name	Description	Version	
CGD985HCI	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2 \times 6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads	SOT115J	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
VB	supply voltage		-	30	V
V _{i(RF)}	RF input voltage	single tone	-	75	dBmV
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM); According JEDEC standard 22-A114E	[1] -	2000	V
		Biased; According IEC61000-4-2	-	1500	V
T _{stg}	storage temperature		-40	+100	°C
T _{mb}	mounting base temperature		-20	+100	°C

[1] The ESD pulse of 2000 V corresponds to a class 2 sensitivity level.

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5. Characteristics

Table 5. Characteristics

Bandwidth 40 MHz to 1003 MHz; $V_B = 24 V (DC)$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35 °C$; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
G _p	power gain	f = 50 MHz		-	23.2	-	dB
		f = 870 MHz		-	24.0	-	dB
		f = 1003 MHz		23.5	24.4	25.5	dB
SL _{sl}	slope straight line	f = 40 MHz to 1003 MHz	[1]	0.5	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 1003 MHz	[2]	-	-	1	dB
RL _{in}	input return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20 - 19 -	-	-	dB
		f = 320 MHz to 640 MHz			-	-	dB
		f = 640 MHz to 870 MHz		17	-	-	dB
		f = 870 MHz to 1003 MHz		16	-	-	dB
RL _{out}	output return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		19	-	-	dB
		f = 640 MHz to 870 MHz		18	-	-	dB
		f = 870 MHz to 1003 MHz		17	-	-	dB
NF	noise figure	f = 50 MHz		-	4.5	5.5	dB
		f = 1003 MHz		-	5	6	dB
I _{tot}	total current		[3]	-	440	460	mA

[1] G_p at 1003 MHz minus G_p at 40 MHz.

[2] Flatness is defined as peak deviation to straight line.

[3] Direct Current (DC).

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
98 PAL [) channels					
СТВ	composite triple beat	$V_o = 48 \text{ dBmV}$ at 862 MHz	<u>[1]</u> -	-66	-62	dBc
		$V_o = 50 \text{ dBmV}$ at 862 MHz	<u>[1]</u> _	-62	-	dBc
CSO	composite second-order distortion	$V_o = 48 \text{ dBmV}$ at 862 MHz	<u>[1]</u> _	-69	-62	dBc
		$V_o = 50 \text{ dBmV}$ at 862 MHz	<u>[1]</u> _	-65	-	dBc
Xmod	cross modulation	$V_o = 48 \text{ dBmV}$ at 862 MHz	<u>[1]</u> _	-68	-	dB
		$V_o = 50 \text{ dBmV}$ at 862 MHz	<u>[1]</u> _	-60	-	dB
112 NTS	C channels					
СТВ	composite triple beat	$V_o = 48 \text{ dBmV}$ at 750 MHz	[2] _	-63	-	dBc
CSO	composite second-order distortion	$V_o = 48 \text{ dBmV}$ at 750 MHz	[2] _	-66	-	dBc
Xmod	cross modulation	$V_o = 48 \text{ dBmV}$ at 750 MHz	[2] _	-66	-	dB
79 NTSC	channels + 75 digital channels					
СТВ	composite triple beat	V _o = 56.4 dBmV at 1003 MHz	<u>[3]</u>	-75	-	dBc
CSO	composite second-order distortion	V _o = 56.4 dBmV at 1003 MHz	<u>[3]</u>	-77	-	dBc
Xmod	cross modulation	V _o = 56.4 dBmV at 1003 MHz	<u>[3]</u>	-68	-	dB
CCN	carrier-to-composite noise	V _o = 56.4 dBmV at 1003 MHz	<u>[3]</u>	57	-	dBc

Table 6.Distortion characteristics

Bandwidth 40 MHz to 1003 MHz; $V_B = 24 V (DC)$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35 °C$; unless otherwise specified.

[1] 98 PAL D channels with 8 MHz bandwidth per channel; [f = 47 MHz to 862 MHz]; flat V_0 till 862 MHz.

[2] 112 NTSC channels; [f = 45 MHz to 750 MHz]; flat V_o till 750 MHz.

[3] 79 NTSC channels [f = 54 MHz to 550 MHz] + 75 digital channels [f = 550 MHz to 1003 MHz] (-6 dB offset); tilt extrapolated to 13.5 dB at 1003 MHz.

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6. Package outline

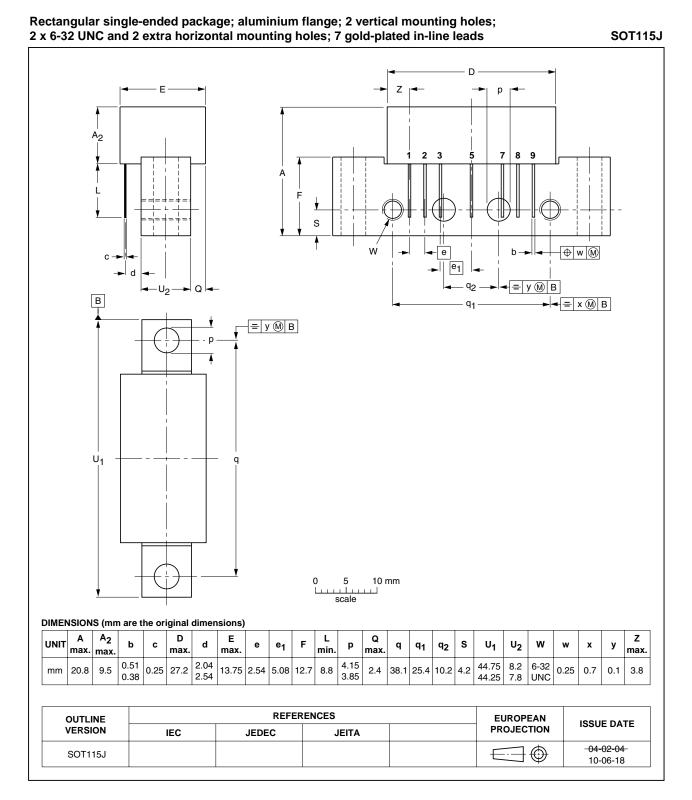


Fig 1. Package outline SOT115J

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7. Abbreviations

Table 7.	Abbreviations
Acronym	Description
CATV	Community Antenna TeleVision
ESD	ElectroStatic Discharge
GaAs	Gallium-Arsenide
NTSC	National Television Standard Committee
PAL	Phase Alternate Line
RF	Radio Frequency
UNC	UNified Coarse

8. Revision history

Table 8. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
CGD985HCI v.1	20110405	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 5 April 2011 Document identifier: CGD985HCI